

STARPOWER

SEMICONDUCTOR

IGBT

GD300CLL170C2S

1700V/300A Chopper in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

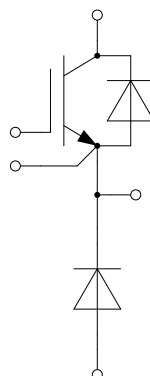
- Low $V_{CE(sat)}$ SPT+ IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175 $^{\circ}$ C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1700	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	430	A
	@ $T_C=100^{\circ}\text{C}$	300	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	600	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	1851	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1700	V
I_F	Diode Continuous Forward Current	300	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	600	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=300\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.40	2.85	V	
		$I_C=300\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.80			
		$I_C=300\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.90			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=12.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.4	6.2	7.4	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			2.3		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		20.0		nF	
C_{res}	Reverse Transfer Capacitance			0.72		nF	
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.8		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=300\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		464		ns	
t_r	Rise Time			157		ns	
$t_{d(off)}$	Turn-Off Delay Time			421		ns	
t_f	Fall Time			290		ns	
E_{on}	Turn-On Switching Loss			108		mJ	
E_{off}	Turn-Off Switching Loss			55.2		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=900\text{V}, I_C=300\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		483		ns
t_r	Rise Time				161		ns
$t_{d(off)}$	Turn-Off Delay Time			465		ns	
t_f	Fall Time			538		ns	
E_{on}	Turn-On Switching Loss			128		mJ	
E_{off}	Turn-Off Switching Loss			83.7		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=300\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			492		ns
t_r	Rise Time				165		ns
$t_{d(off)}$	Turn-Off Delay Time			483		ns	
t_f	Fall Time			747		ns	
E_{on}	Turn-On Switching Loss			141		mJ	
E_{off}	Turn-Off Switching Loss			92.1		mJ	
I_{SC}	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=1000\text{V}, V_{CEM} \leq 1700\text{V}$		960		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=300\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.80	2.25	V
		$I_F=300\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.95		
		$I_F=300\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.90		
Q_r	Recovered Charge	$V_R=900\text{V}, I_F=300\text{A},$ $-di/dt=2800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		70		μC
I_{RM}	Peak Reverse Recovery Current			209		A
E_{rec}	Reverse Recovery Energy			40.7		mJ
Q_r	Recovered Charge	$V_R=900\text{V}, I_F=300\text{A},$ $-di/dt=2800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		108		μC
I_{RM}	Peak Reverse Recovery Current			238		A
E_{rec}	Reverse Recovery Energy			65.1		mJ
Q_r	Recovered Charge	$V_R=900\text{V}, I_F=300\text{A},$ $-di/dt=2800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		123		μC
I_{RM}	Peak Reverse Recovery Current			253		A
E_{rec}	Reverse Recovery Energy			71.6		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.081	K/W
	Junction-to-Case (per Diode)			0.138	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.022		K/W
	Case-to-Heatsink (per Diode)		0.037		
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

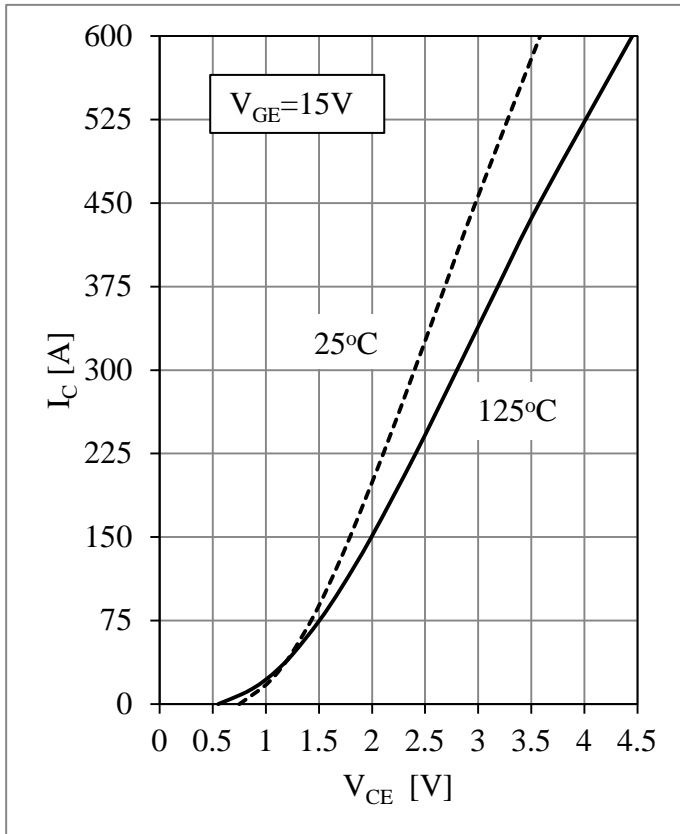


Fig 1. IGBT Output Characteristics

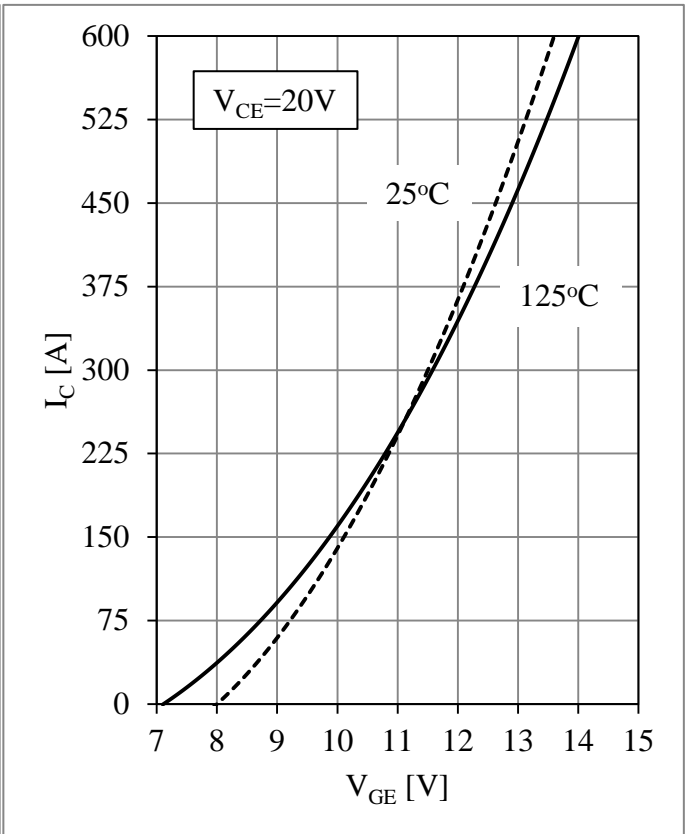


Fig 2. IGBT Transfer Characteristics

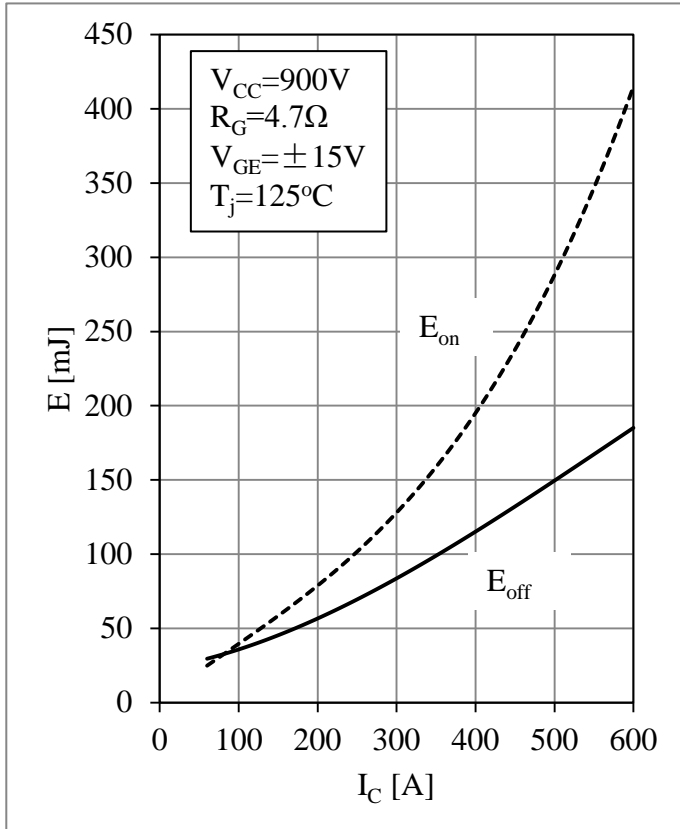


Fig 3. IGBT Switching Loss vs. I_C

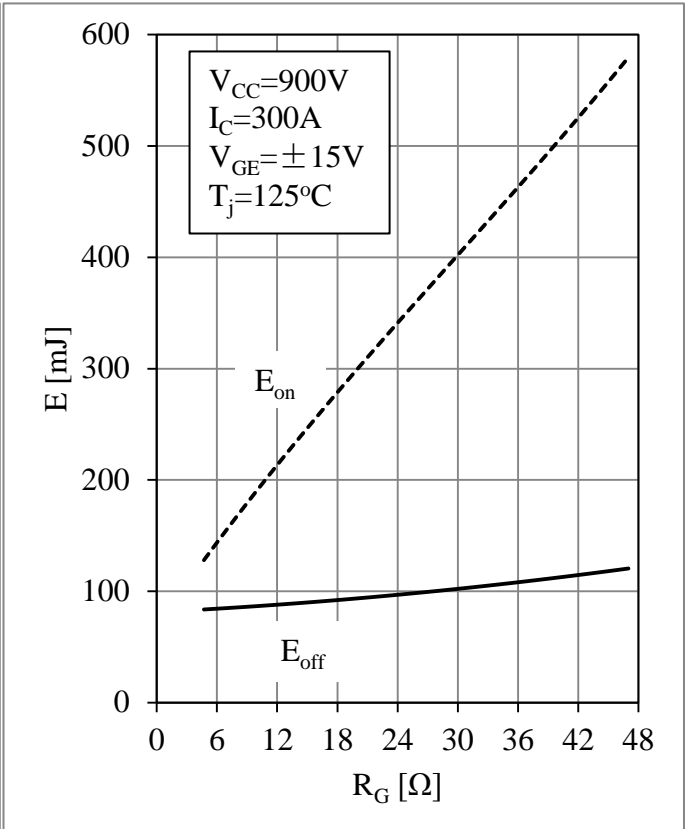


Fig 4. IGBT Switching Loss vs. R_G

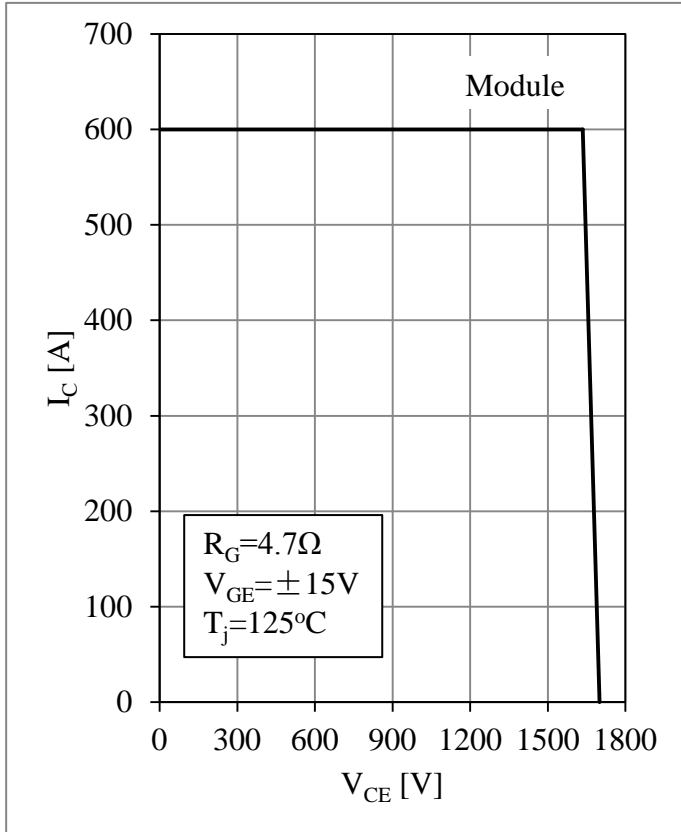


Fig 5. RBSOA

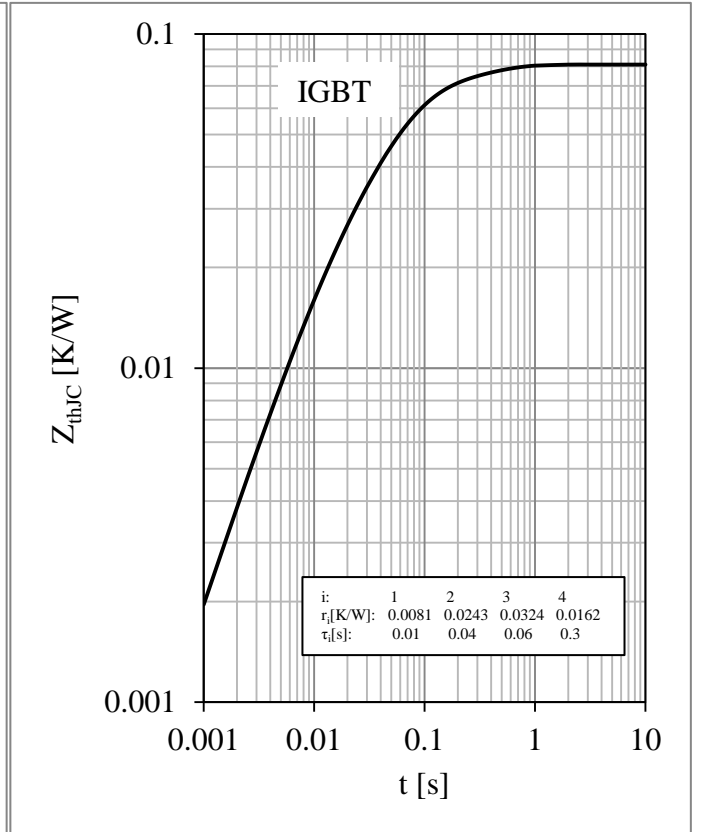


Fig 6. IGBT Transient Thermal Impedance

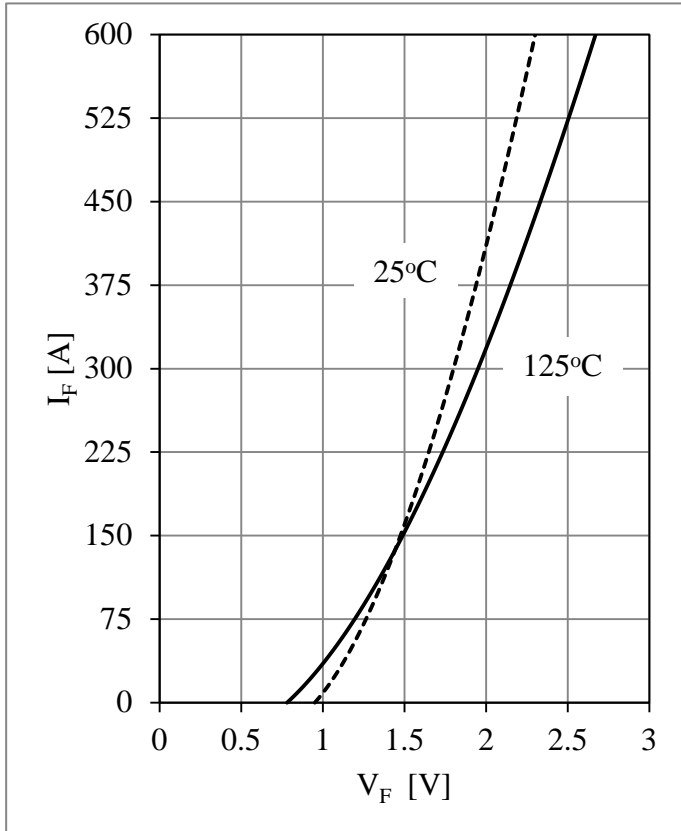


Fig 7. Diode Forward Characteristics

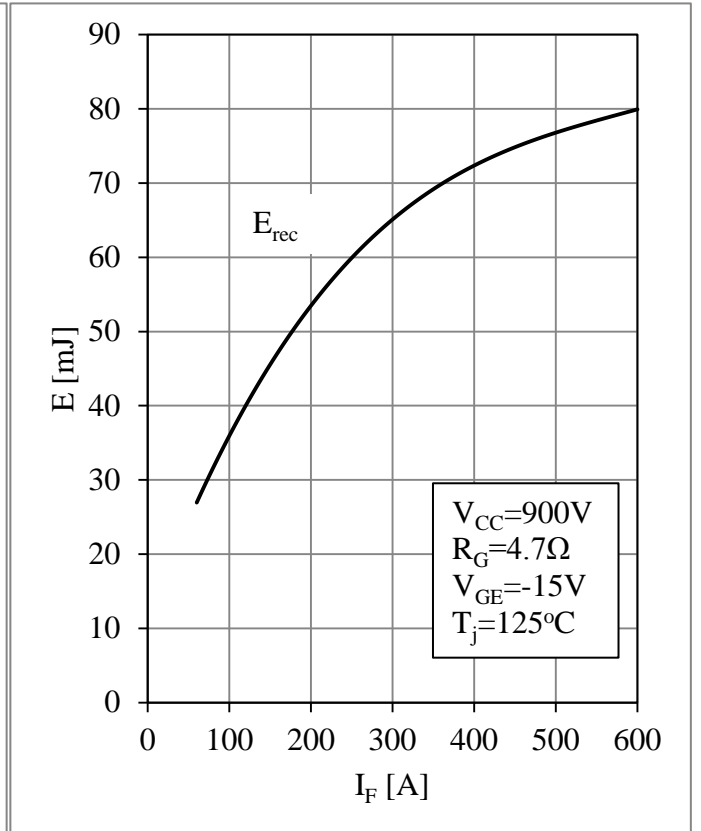


Fig 8. Diode Switching Loss vs. I_F

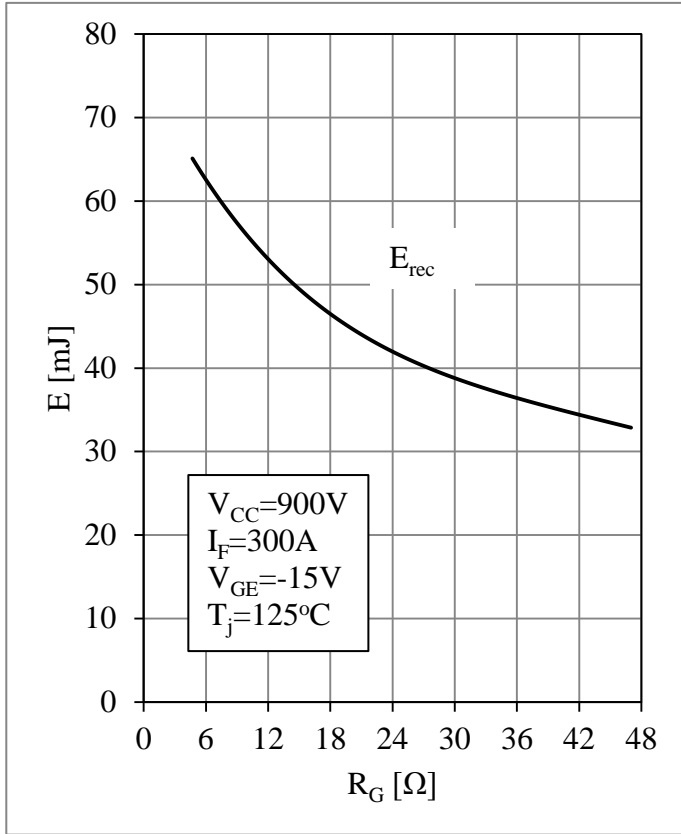


Fig 9. Diode Switching Loss vs. R_G

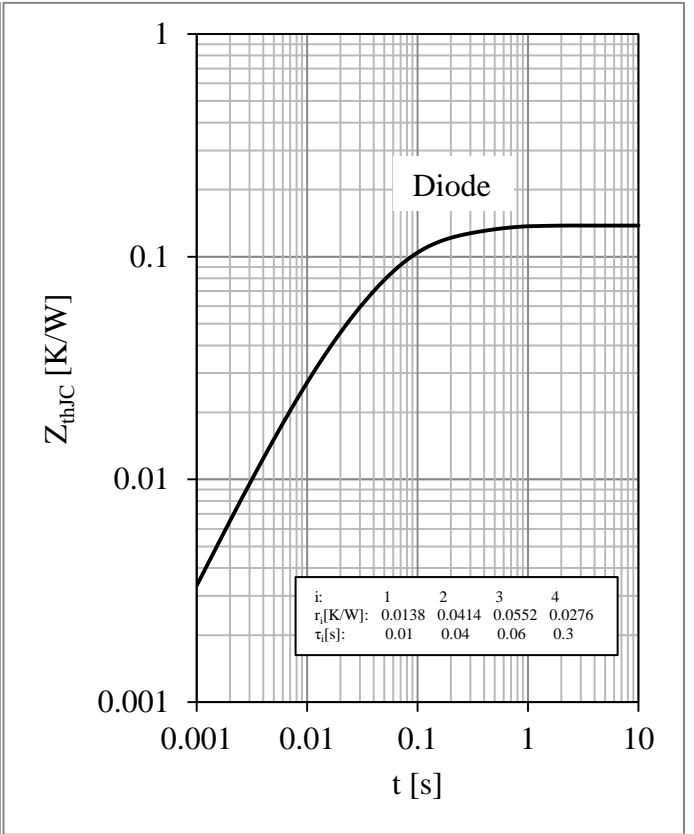
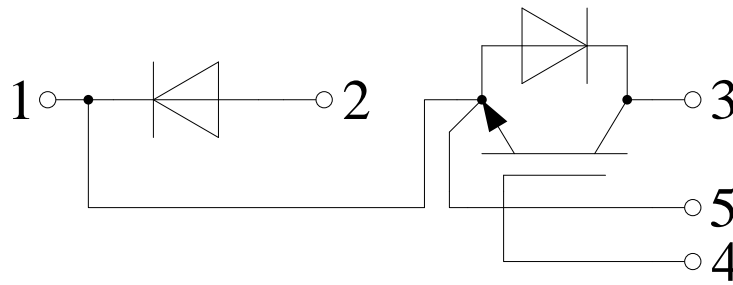


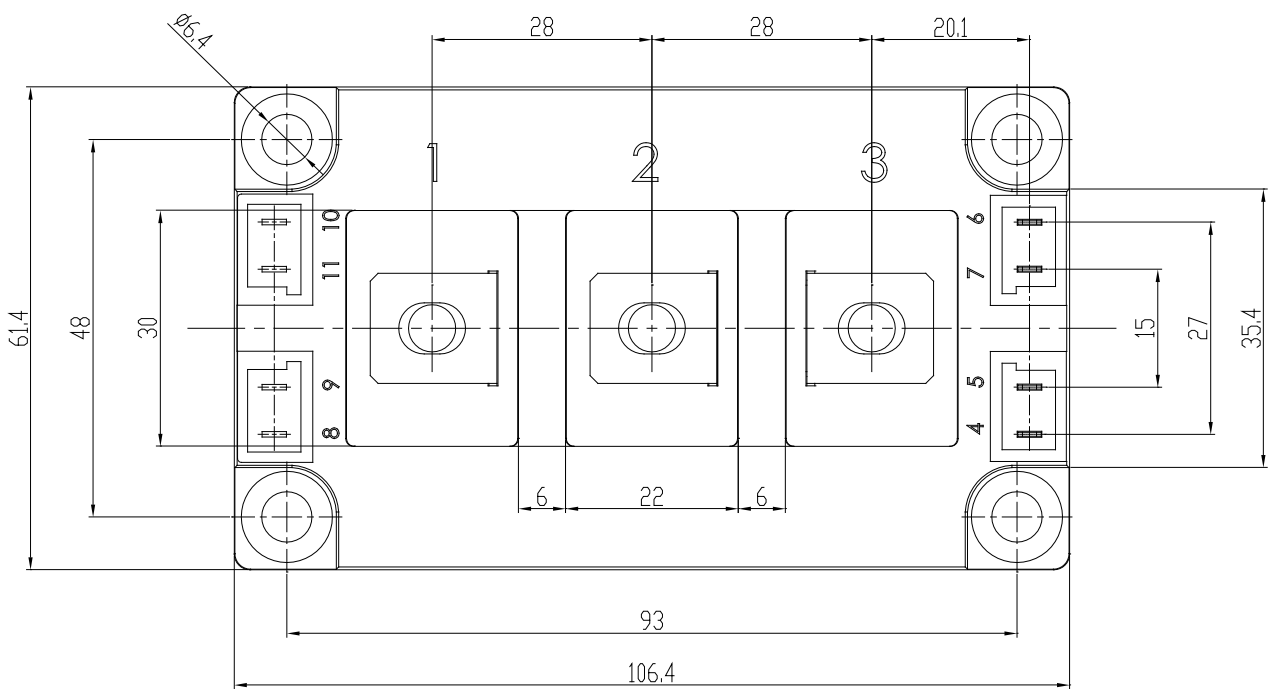
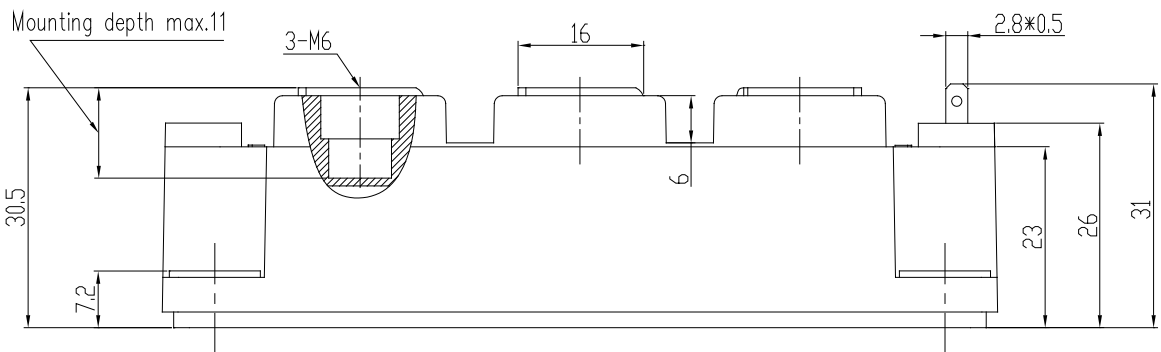
Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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